

FORM PTO-1449
INFORMATION DISCLOSURE
STATEMENT BY APPLICANT(S)

Atty Docket No.: 2369/23
 Serial No. :
 Applicants : K. NAKAZATO et al.
 Filed :
 Group Art Unit:
 Examiner :



U.S. PATENT DOCUMENTS

Examiner Initial	Patent Number	Patent Date	Name	Class/ Subclass	Filing Date
EO	3,878,549	04/15/75	YAMAZAKI et al.	357/23	09/11/73
EO	5,604,357	02/97	HORI	257/324	
EO	5,286,994	02/94	OZAWA et al.	257/324	
EO	5,319,229	06/94	SHIMOJI et al.	257/324	
EO	5,216,262	06/93	TSU	257/411	

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class/ Subclass	Translation Yes No
EO	2 111 866	06/09/72	France		ABS.
EO	0 642 173	03/08/95	EPO		N/A
EO	WO 94/15340	07/07/94	Great Britain		N/A

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner
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|---------------------------|---|
| <p>_____</p> <p>_____</p> | <p>1. IEEE TRANSACTIONS ON ELECTRON DEVICES, Vol. 43, No. 9, Sept. 1996, pp. 1553-1558, Hanati et al.; <i>Fast and Long Retention-Time Nano-Crystal Memory</i></p> <p>2. MICROELECTRONIC ENGINEERING, Vol. 32, No. 1/04, Sept. 1996, pp. 297-315, H. Ahmed et al.: <i>Single-Electron Devices</i></p> |
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K. Nakazato et al.

10/16/01

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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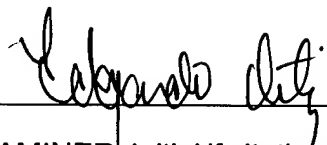
(Including Author, Title, Date, Pertinent Pages, Etc.)

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| <p>_____</p> <p>_____</p> <p>_____</p> <p>_____</p> <p>_____</p> | <p>3. PHYSICAL REVIEW, B. CONDENSED MATTER, Vol. 50, No. 12, 15 Sept. 1994, pp. 8961-8964, Bar-Sadeh et al.: <i>Single-Electron Tunneling Effects in Granular Metal Films</i></p> <p>4. IEEE TRANSACTIONS ON ELECTRON DEVICES, Vol. 41, No. 9, Sept. 1994, pp. 1628-1638, K. Yano et al.: <i>Room-Temperature Single-Electron Memory</i></p> <p>5. 1996 IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, pp. 266-268, K. Yano et al.: <i>Single-Electron-Memory Integrated Circuit for Giga-to-Tera Bit Storage</i></p> <p>6. APPL. PHYS. LETT. 68 (10), 4 March 1996, pp. 1377-1379, Sandip Tiwan et al.: <i>A Silicon Nanocrystals-based Memory</i></p> <p>7. IEEE ELECTRON DEVICE LETTERS, Vol. EDL 1, No. 9, September 1980, pp. 179-181, DiMaria et al.: <i>Electrically-Alterable Memory Using A Duel Electron Injector Structure</i></p> |
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